## N-Channel 190-V (D-S) MOSFET

### **Key Features:**

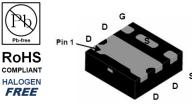
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

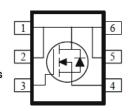
### **Typical Applications:**

- · Boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

| PRODUCT SUMMARY     |                       |        |  |
|---------------------|-----------------------|--------|--|
| V <sub>DS</sub> (V) | $r_{DS(on)}(m\Omega)$ | I□ (A) |  |
| 190                 | $1.8 @ V_{GS} = 10V$  | 1.9    |  |
|                     | $2.4 @ V_{GS} = 4.5V$ | 1.7    |  |

DFN1.6x1.6-6L





| ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED) |                      |                   |                  |       |  |  |
|---|----------------------|-------------------|------------------|-------|--|--|
| Parameter   |                      |                   | Limit            | Units |  |  |
| Drain-Source Voltage  |                      |                   | 190              | V     |  |  |
| Gate-Source Voltage   |                      |                   | ±20              | V     |  |  |
|   | T <sub>C</sub> =25°C |                   | 1.9              | A     |  |  |
| Continuous Drain Current  | T <sub>C</sub> =70°C | l <sub>D</sub>    | 1.6              |       |  |  |
| Continuous Diairi Curient   | T <sub>A</sub> =25°C |                   | 0.9 <sup>a</sup> |       |  |  |
|   | T <sub>A</sub> =70°C |                   | 0.7 <sup>a</sup> |       |  |  |
| Pulsed Drain Current <sup>b</sup>                                       | I <sub>DM</sub>      | 5                 |                  |       |  |  |
| Continuous Source Current (Diode Conduction) a                          | I <sub>S</sub>       | 0.9               |                  |       |  |  |
|   | T <sub>C</sub> =25°C |                   | 9.6              | W     |  |  |
| Power Dissipation   | T <sub>C</sub> =70°C | $P_{D}$           | 6.2              |       |  |  |
| r ower dissipation  | T <sub>A</sub> =25°C | ' D               | 1.8 <sup>a</sup> |       |  |  |
|   | T <sub>A</sub> =70°C |                   | 1.2 <sup>a</sup> |       |  |  |
| Operating Junction and Storage Temperature Range                        |                      | $T_J$ , $T_{stg}$ | -55 to 150       | °C    |  |  |

| THERMAL RESISTANCE RATINGS               |              |                   |       |      |  |  |  |
|--|--------------|-------------------|-------|------|--|--|--|
| Parameter                                | Symbol       | Maximum           | Units |      |  |  |  |
| Maximum Junction-to-Ambient <sup>a</sup> | t <= 10 sec  | $R_{\theta JA}$   | 70    | °C/W |  |  |  |
| IMAXIMUM JUNCIION-IO-AMBIENI             | Steady State | Γ <sub>θ</sub> JA | 110   |      |  |  |  |
| Maximum Junction-to-Case                 | Steady State | $R_{\theta JC}$   | 13    |      |  |  |  |

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

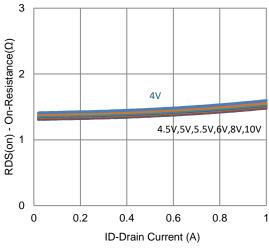
| Parameter                               | Symbol              | Test Conditions  | Min | Тур  | Max   | Unit |  |
|---|---------------------|--|-----|------|-------|------|--|
| Static                                  |                     |  |     |      |       |      |  |
| Gate-Source Threshold Voltage           | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$                                       | 1   |      |       | V    |  |
| Gate-Body Leakage                       | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                                |     |      | ±100  | nA   |  |
| Zero Gate Voltage Drain Current         | lane                | $V_{DS} = 152 \text{ V}, V_{GS} = 0 \text{ V}$                                   |     |      | 1     | uA   |  |
| Zero Gate Voltage Brain Gurrent         | I <sub>DSS</sub>    | $V_{DS} = 152 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$       |     |      | 10    | uA   |  |
| On-State Drain Current <sup>a</sup>     | I <sub>D(on)</sub>  | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$                                    | 1.5 |      |       | Α    |  |
| Drain-Source On-Resistance <sup>a</sup> | r                   | $V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$                                     |     |      | 1.8 Ω |      |  |
| Drain-Source On-Resistance              | r <sub>DS(on)</sub> | $V_{GS} = 4.5 \text{ V}, I_D = 0.4 \text{ A}$                                    |     |      | 2.4   | 12   |  |
| Forward Transconductance <sup>a</sup>   | g <sub>fs</sub>     | $V_{DS} = 15 \text{ V}, I_{D} = 0.5 \text{ A}$                                   |     | 1    |       | S    |  |
| Diode Forward Voltage <sup>a</sup>      | $V_{SD}$            | $I_S = 0.45 \text{ A}, V_{GS} = 0 \text{ V}$                                     |     | 0.77 |       | V    |  |
|   |                     | Dynamic <sup>b</sup>   |     |      |       |      |  |
| Total Gate Charge                       | $Q_g$               | $V_{DS} = 95 \text{ V}, V_{GS} = 4.5 \text{ V},$                                 |     | 4.5  |       |      |  |
| Gate-Source Charge                      | $Q_{gs}$            | $I_{DS} = 93 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 0.5 \text{ A}$ |     | 1.1  |       | nC   |  |
| Gate-Drain Charge                       | $Q_{gd}$            | 1B = 0.5 A   |     | 1.9  |       |      |  |
| Turn-On Delay Time                      | t <sub>d(on)</sub>  | $V_{DS} = 95 \text{ V}, R_1 = 190 \Omega,$                                       |     | 5    |       |      |  |
| Rise Time                               | t <sub>r</sub>      | $V_{DS} = 95 \text{ V}, \text{ K}_{L} - 190 \Omega,$ $I_{D} = 0.5 \text{ A},$    |     | 6    |       | no   |  |
| Turn-Off Delay Time                     | $t_{d(off)}$        | $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$                                     |     | 21   |       | ns   |  |
| Fall Time                               | t <sub>f</sub>      | V GEN = 10 V, 1 (GEN = 0.12  |     | 12   |       |      |  |
| Input Capacitance                       | C <sub>iss</sub>    |  |     | 245  |       |      |  |
| Output Capacitance                      | C <sub>oss</sub>    | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$                 |     | 18   |       | pF   |  |
| Reverse Transfer Capacitance            | $C_{rss}$           |  |     | 17   |       |      |  |

#### Notes

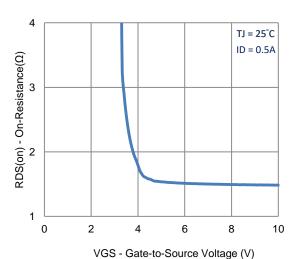
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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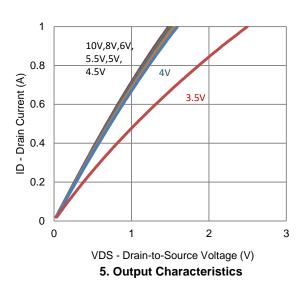
### **Typical Electrical Characteristics**

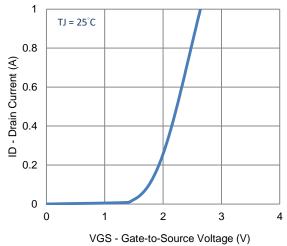


#### 1. On-Resistance vs. Drain Current

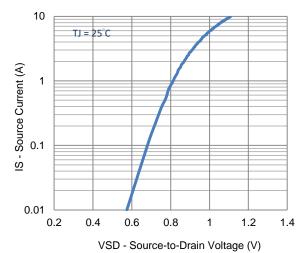


3. On-Resistance vs. Gate-to-Source Voltage

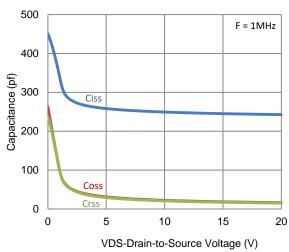




2. Transfer Characteristics

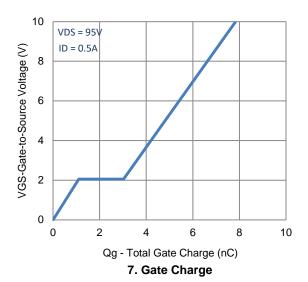


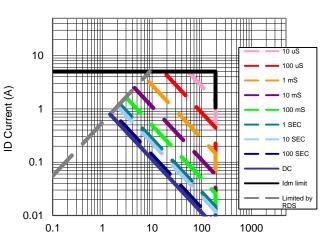
4. Drain-to-Source Forward Voltage



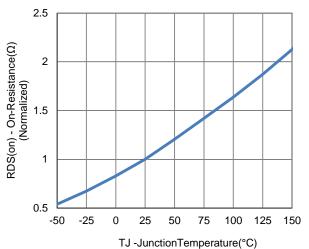
6. Capacitance

### **Typical Electrical Characteristics**

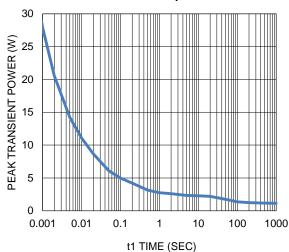




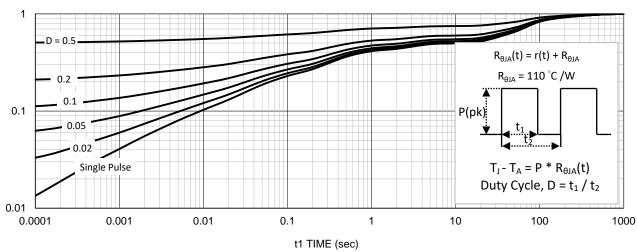




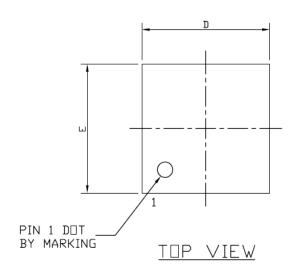
8. Normalized On-Resistance Vs Junction Temperature

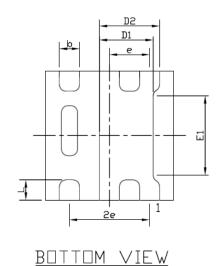


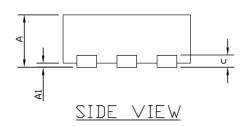
10. Single Pulse Maximum Power Dissipation



# Package Information







| SYMBOLS DIMENSIONS IN MILLIMETERS |            | DIMENSIONS IN INCHES |      |            |       |       |  |
|-----------------------------------|------------|----------------------|------|------------|-------|-------|--|
| SIMBULS                           | MIN        | NDM                  | MAX  | MIN        | NDM   | MAX   |  |
| Α                                 | 0.50       | 0.55                 | 0.60 | 0.020      | 0.022 | 0.024 |  |
| A1                                | 0.00       |                      | 0.05 | 0.000      |       | 0.002 |  |
| b                                 | 0.22       | 0.25                 | 0.28 | 0.009      | 0.010 | 0.011 |  |
| С                                 | 0.152 Ref. |                      |      | 0.006 Ref. |       |       |  |
| D                                 | 1.55       | 1.60                 | 1.65 | 0.061      | 0.063 | 0.065 |  |
| D1                                | 0.67 TYP   |                      |      | 0.026 TYP  |       |       |  |
| D2                                | 0.75 TYP   |                      |      | 0.030 TYP  |       |       |  |
| E                                 | 1.55       | 1.60                 | 1.65 | 0.061      | 0.063 | 0.065 |  |
| E1                                | 0.98 TYP   |                      |      | 0.039 TYP  |       |       |  |
| е                                 |            | 0.50 BSC 0.020 BSC   |      |            |       |       |  |
| L                                 | 0.20       | 0.25                 | 0.30 | 0.008      | 0.010 | 0.012 |  |

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